

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

1 (currently amended): A light emitting device comprising:

- 5           a micro-reflection structure carrier having a plurality of concave surfaces;  
          a reflection layer formed conformably to said plurality of concave surfaces;  
          a first reaction layer formed over the reflection layer;  
          a transparent adhesive layer formed over the first reaction layer ~~reflection layer~~;  
          and  
10          a light emitting stack layer formed over the transparent adhesive layer, the light  
          emitting stack layer comprising:  
          a second reaction layer formed over the transparent adhesive layer;  
          a first transparent conductive layer formed over the second reaction layer;  
          a first contact layer formed over the transparent conductive layer;  
15          a first cladding layer formed between the first contact layer and the light  
          emitting layer;  
          a second cladding layer formed over the light emitting layer;  
          a second contact layer formed over the second cladding layer;  
          a first electrode; and  
20          a second electrode formed over the second contact layer.

2 (cancelled).

- 3 (previously presented): The light emitting device of claim 1 further comprising a  
25          reaction layer between the transparent adhesive layer and the light emitting stack layer.

4 (original): The light emitting device of claim 1 further comprising a first electrode and a

second electrode formed on the same upper surface of the light emitting stack layer.

5 (withdrawn): The light emitting device of claim 1 further comprising a first electrode  
and a second electrode formed on the upper surface of the light emitting stack layer and  
5 the lower surface of the micro-reflection structure carrier respectively.

6 (cancelled).

7 (currently amended): The light emitting device of ~~claim 6~~ claim 1, wherein the  
10 transparent conductive layer has a first surface area and a second surface area, the first  
contact layer is formed over the first surface area, and the first electrode is formed over  
the second surface area.

8 (original): The light emitting device of claim 7 further comprising a transparent carrier  
15 between the second reaction layer and the transparent conductive layer.

9 (withdrawn - currently amended): The light emitting device of ~~claim 6~~ claim 1, wherein  
the micro-reflection structure carrier is a conductive micro-reflection structure carrier,  
the transparent adhesive layer is a transparent conductive adhesive layer, and the first  
20 electrode is formed over a lower surface of the conductive micro-reflection structure  
carrier.

10 (currently amended): The light emitting device of claim 1, wherein the shape of the  
micro-reflection structure carrier comprises ~~at least one shape selected from a group~~  
25 ~~consisting of a hemisphere and a pyramid.~~

11 (original): The light emitting device of claim 1, wherein the micro-reflection structure  
carrier comprises at least one material selected from a group consisting of GaP, GaAs,

GaAsP, InGaP, AlGaInP, AlGaAs, Si, SiC, glass, BN, AlN, and Ge.

12 (withdrawn): The light emitting device of claim 9, wherein the conductive  
micro-reflection structure carrier comprises at least one material selected from a  
5 group consisting of Si, GaAs, SiC, GaP, GaAsP, InGaP, AlGaInP, AlGaAs, BN, and  
AlN.

13 (original): The light emitting device of claim 8, wherein the transparent carrier  
comprises at least one material selected from a group consisting of GaP, SiC, Al<sub>2</sub>O<sub>3</sub>,  
10 and glass.

14 (original): The light emitting device of claim 1, wherein the reflection layer comprises  
at least one material selected from a group consisting of Sn, Al, Au, Pt, Zn, Ag, Ti, Pb,  
Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, and AuZn.

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15-16 (cancelled).

17 (previously presented): The light emitting device of claim 3, wherein the reaction layer  
comprises at least one material selected from a group consisting of SiNx, Ti, and Cr.  
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18 (currently amended): The light emitting device of ~~claim 6~~ claim 1, wherein the second  
reaction layer comprises at least one material selected from a group consisting of  
SiNx, Ti, and Cr.

25 19 (withdrawn): The light emitting device of claim 9, wherein the transparent conductive  
adhesive layer comprises at least one conductive material selected from a group  
consisting of intrinsically conducting polymer, and polymer mixed with conducting  
material.

20 (withdrawn): The light emitting device of claim 19, wherein the conducting material comprises at least one material selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, zinc tin oxide, Au, and Ni/Au.

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21 (currently amended): The light emitting device of ~~claim 6~~ claim 1, wherein the first cladding layer comprises at least one material selected from a group consisting of AlGaInP, AlN, GaN, AlGaN, InGaN, and AlInGaN.

10 22 (currently amended): The light emitting device of ~~claim 6~~ claim 1, wherein the light emitting layer comprises at least one material selected from a group consisting of AlGaInP, GaN, InGaN, and AlInGaN.

15 23 (currently amended): The light emitting device of ~~claim 6~~ claim 1, wherein the second cladding layer comprises at least one material selected from a group consisting of AlGaInP, AlN, GaN, AlGaN, InGaN, and AlInGaN.

20 24 (currently amended): The light emitting device of ~~claim 6~~ claim 1, wherein the first contact layer comprises at least one material selected from a group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, AlGaAs, GaN, InGaN, and AlGaN.

25 25 (currently amended): The light emitting device of ~~claim 6~~ claim 1, wherein the second contact layer comprises at least one material selected from a group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, AlGaAs, GaN, InGaN, and AlGaN.

26 (currently amended): The light emitting device of ~~claim 6~~ claim 1, wherein a second transparent conductive layer is formed between the second electrode and the second contact layer.

27 (currently amended): The light emitting device of ~~claim 6~~ claim 1, wherein the first transparent conductive layer comprises at least one material selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, and zinc tin oxide.

28 (original): The light emitting device of claim 26, wherein the second transparent conductive layer comprises at least one material selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, and zinc tin oxide.

29 (new): A light emitting device comprising:

- a micro-reflection structure carrier having a plurality of concave surfaces;
- a reflection layer formed conformably to said plurality of concave surfaces;
- a transparent adhesive layer formed over the reflection layer, wherein the transparent adhesive layer comprises at least one material selected from a group consisting of polyimide (PI), benzocyclobutene (BCB), and perfluorocyclobutane (PFCB); and
- a light emitting stack layer formed over the transparent adhesive layer.

30 (new): A light emitting device comprising:

- a micro-reflection structure carrier having a plurality of concave surfaces;
- a reflection layer formed conformably to said plurality of concave surfaces;
- a first reaction layer formed over the reflection layer, wherein the first reaction layer comprises at least one material selected from a group consisting of SiNx, Ti, and Cr;
- a transparent adhesive layer formed over the first reaction layer; and
- a light emitting stack layer formed over the transparent adhesive layer.